UP05C8PG

Silicon NPN epitaxial planar type (Tr) Silicon epitaxial planar type (CCD load device)

For CCD output circuits

Features

- Two elements incorporated into one package (Tr + CCD load device)
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

Basic Part Number

• 2SC3932G + CCD load device

Absolute Maximum Ratings $T_a = 25^{\circ}C$

	Parameter	Symbol	Rating	Unit	
Tr	Collector-base voltage (Emitter open)	V _{CBO}	30	V	
	Collector-emitter voltage (Base open)	V _{CEO}	20	V	
	Emitter-base voltage (Collector open)	V _{EBO}	3	v	
	Collector current	I _C	50	mA	
CCD load device	Limiting element voltage	V _{max}	40	S V	
	Limiting element current	I _{max}	.10	mA	
Overall	Total power dissipation *	P _T	125	mW	
	Junction temperature	Tj	125	 C 	
	Storage temperature	T _{stg}	-55 to +125	°C	

Note) * : Measuring on substrate at 17 mm \times 10 mm \times 1 mm

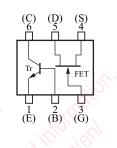
2: Base5: Drain3: Gate6: Collector

PackageCode

SSMini6-F2 • Pin Name

1: Emitter

- Marking Symbol: 4X
- Internal Connection



4: Source

Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

• Tr

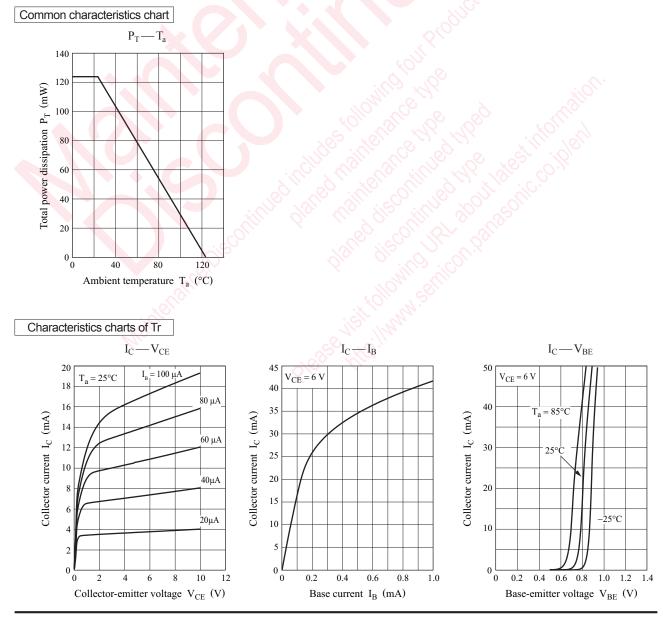
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_{\rm C} = 100 \ \mu A, I_{\rm E} = 0$	30			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = 10 \ \mu {\rm A}, \ I_{\rm C} = 0$	3			V
Base-emitter voltage	V _{BE}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$		720		mV
Forward current transfer ratio	h _{FE}	$V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$	100		250	
Transition frequency *	f_{T}	$V_{CB} = 10 \text{ V}, I_E = -15 \text{ mA}, f = 200 \text{ MHz}$		1 300		MHz
Power gain	G _P	$V_{CB} = 10 \text{ V}, I_E = -1 \text{ mA}, f = 100 \text{ MHz}$		20		dB

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. *: Pulse measurement

CCD Load Device

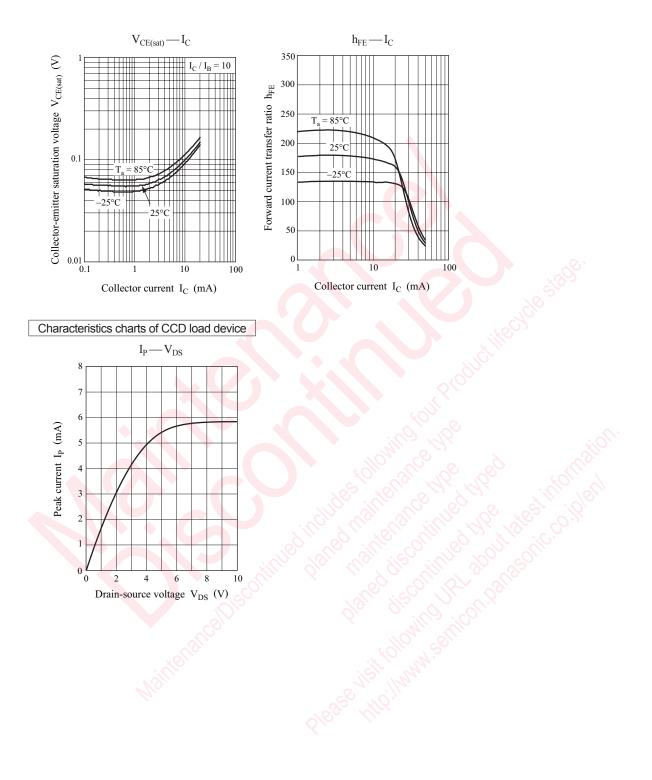
Parameter	Symbol		Conditions	Min	Тур	Max	Unit
Pinchi off current	Ip	V _{DS} =	$= 8 V, V_G = 0$	5.0	R.	7.0	mA
Output impedance	Zo	V _{DS} =	$= V, V_G = 0$	i on	0.02		MΩ

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



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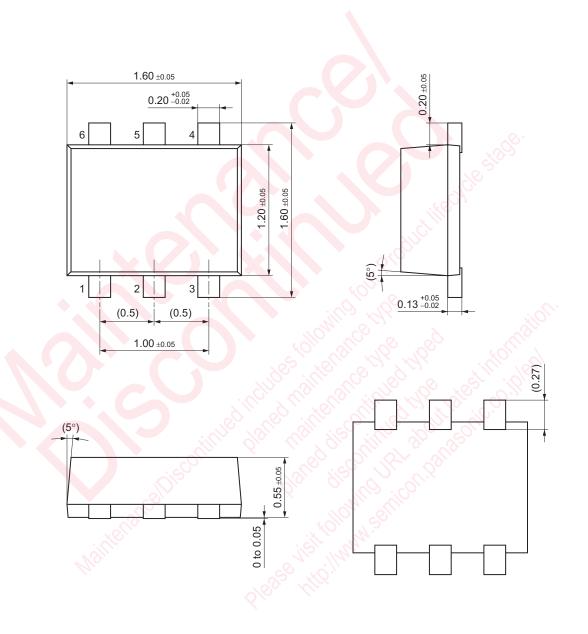
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SSMini6-F2

Unit: mm



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